

Applications for isolated gate drivers

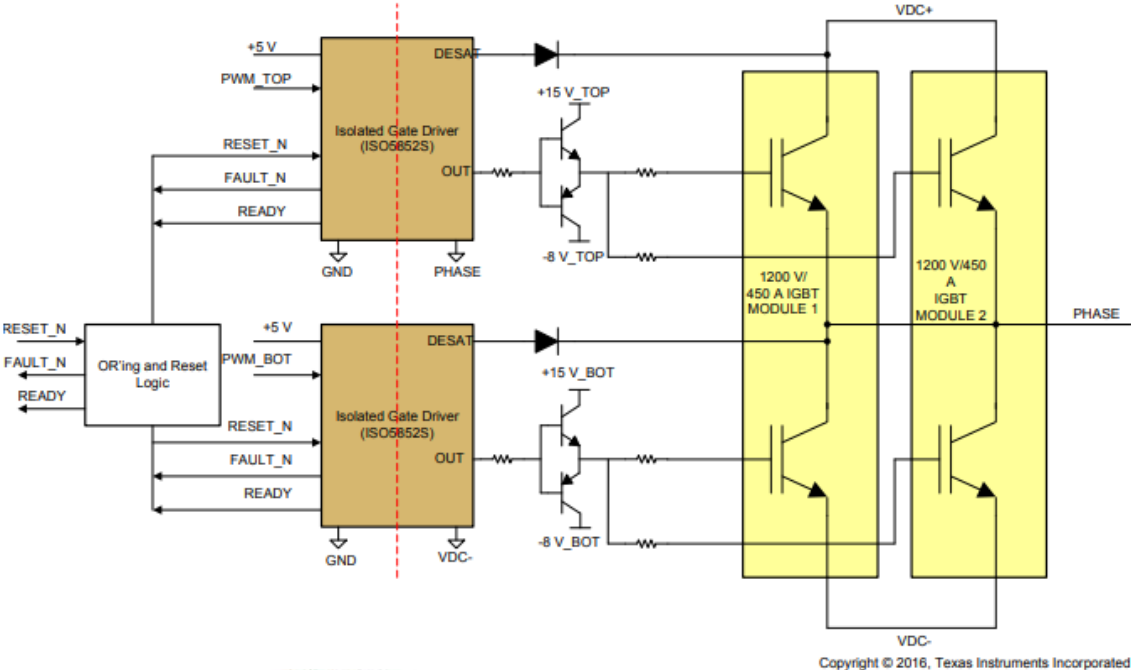
TIPL 502

TI Precision Labs – Isolated Gate Drivers

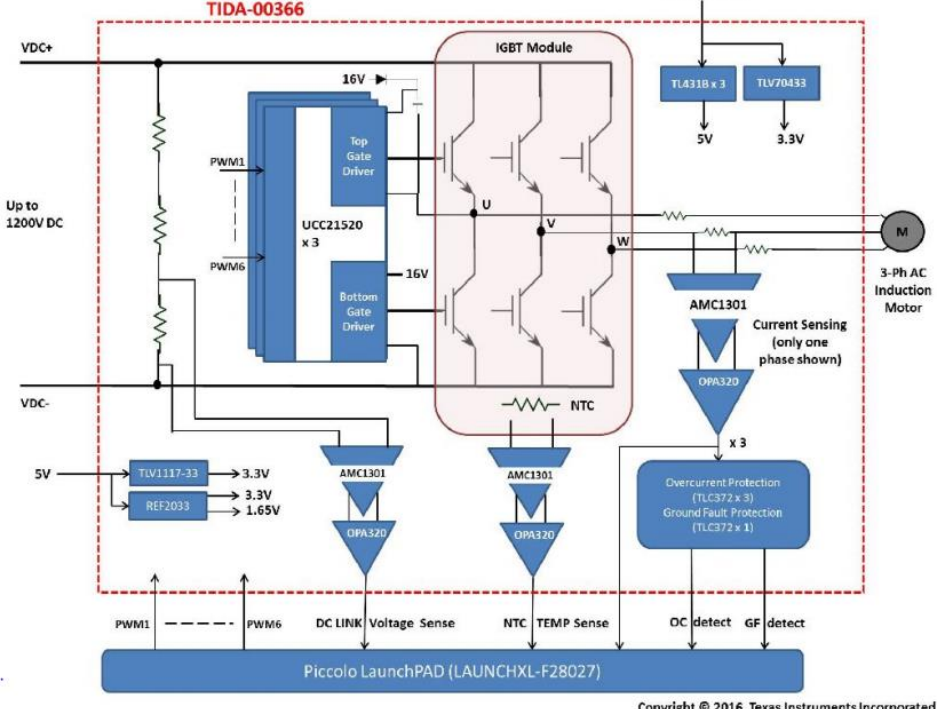
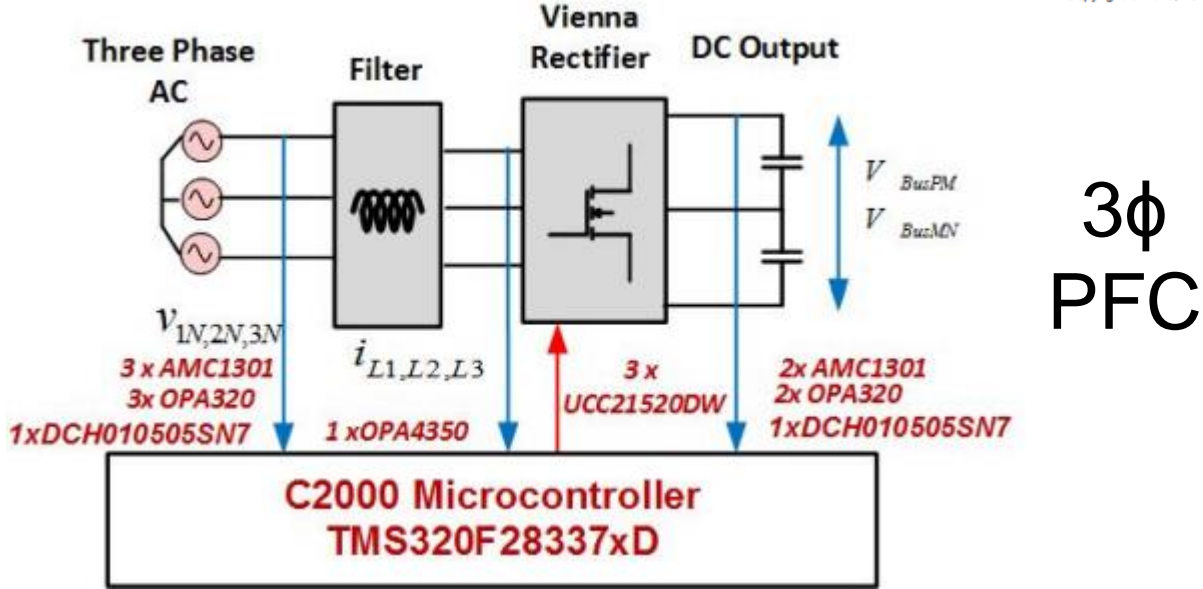
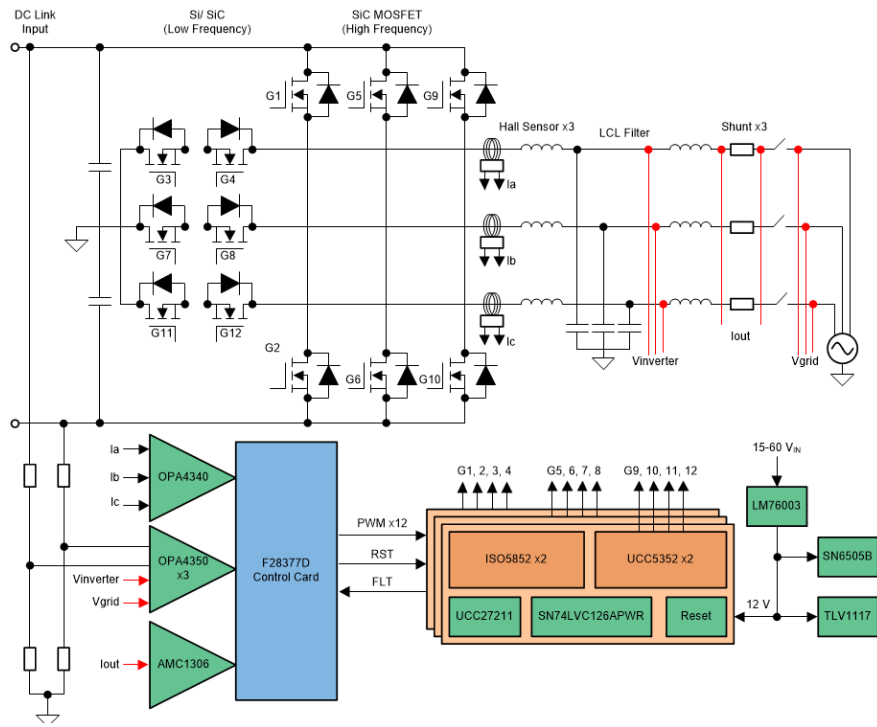
Presented and Prepared by Derek Payne

Example Topologies

Traction Inverter

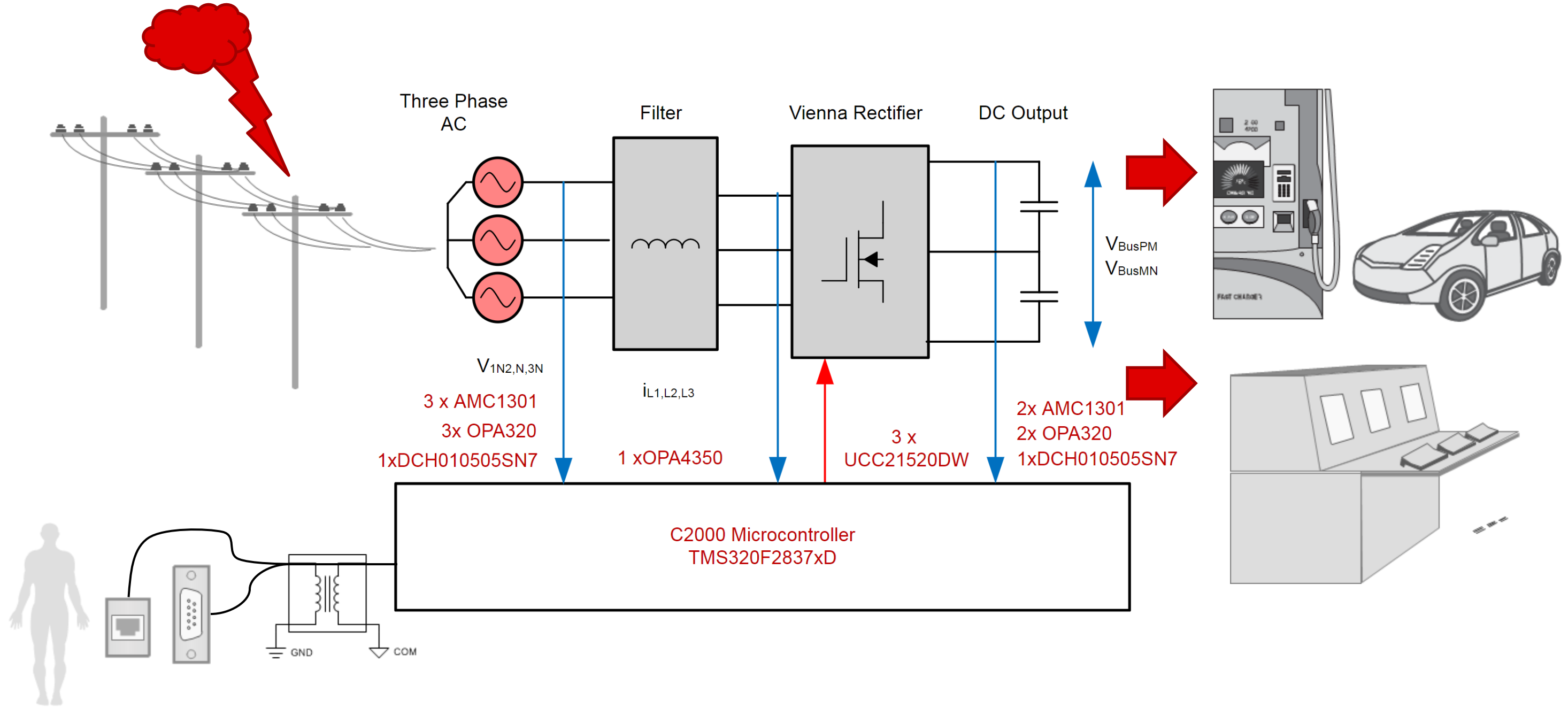


Solar String Inverter

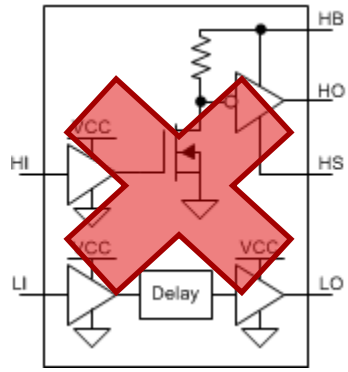


Motor Drive

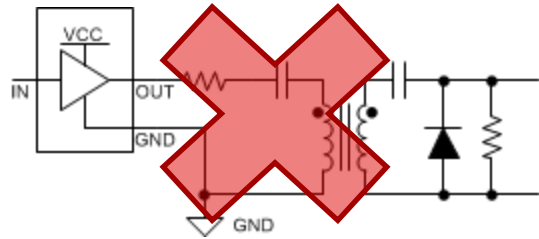
Three Phase Power Factor Correction



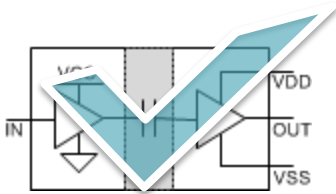
Three Phase Power Factor Correction



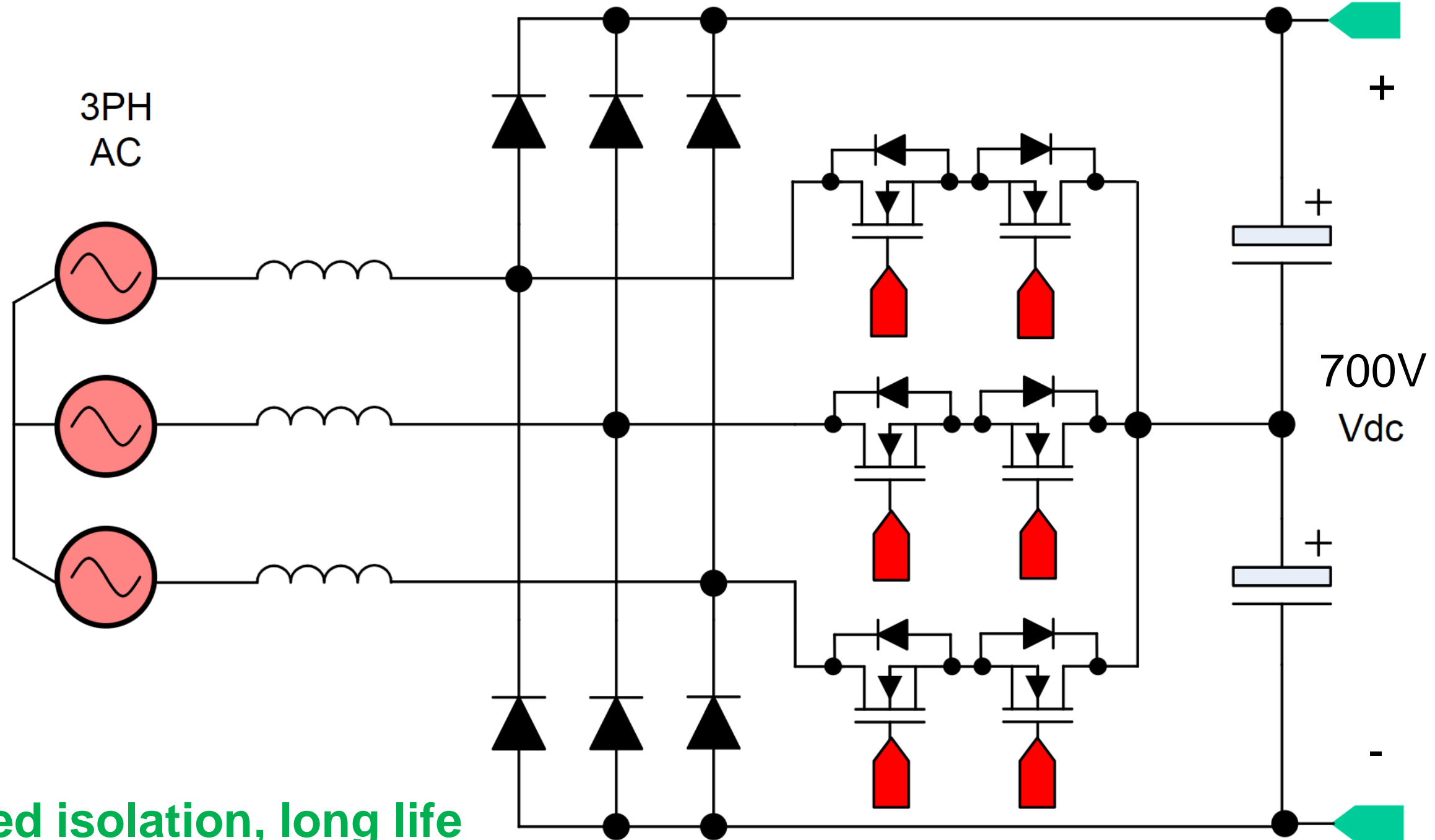
600V Abs. Max



Cost, Space, Effort



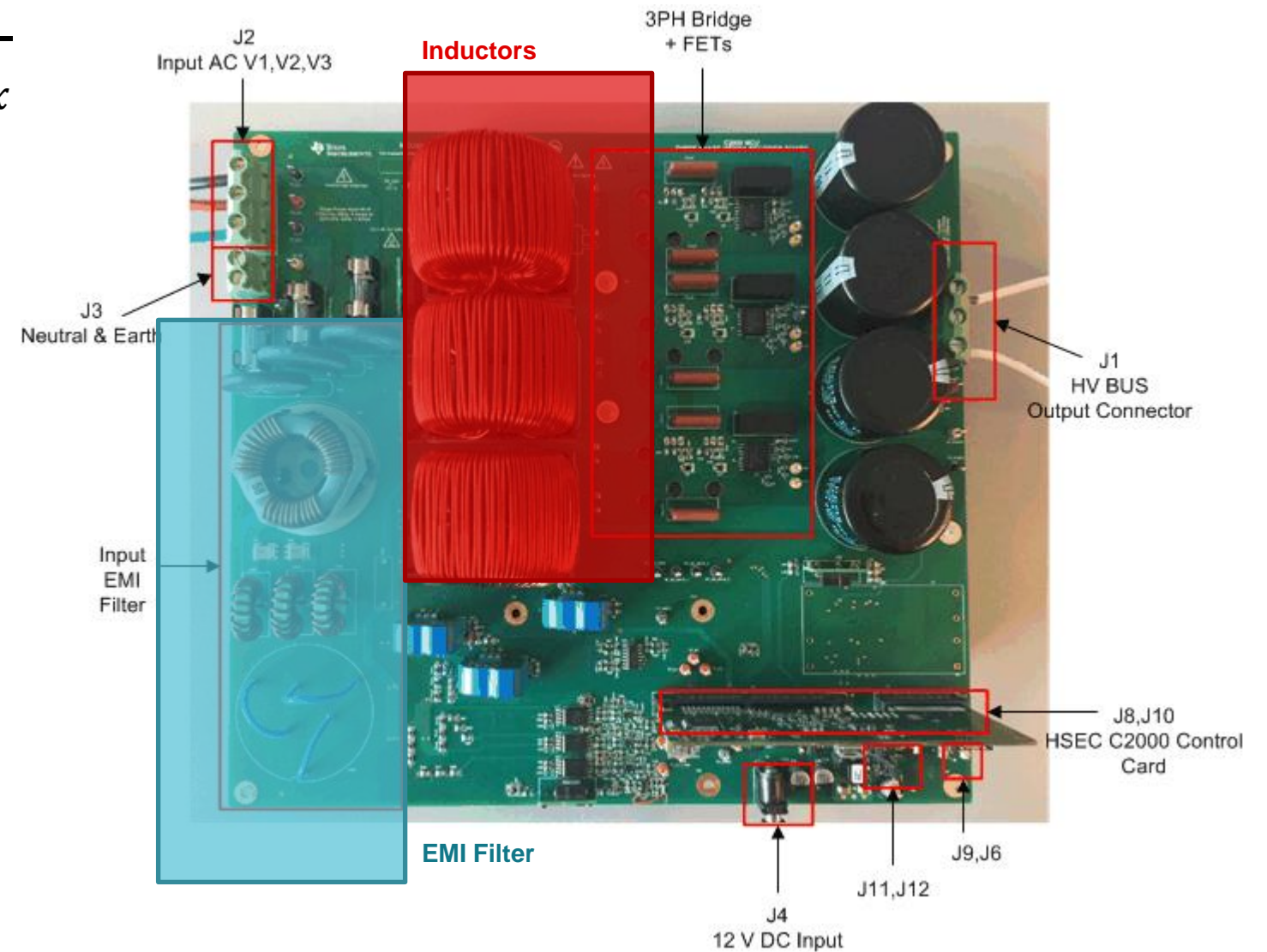
Compact, reinforced isolation, long life



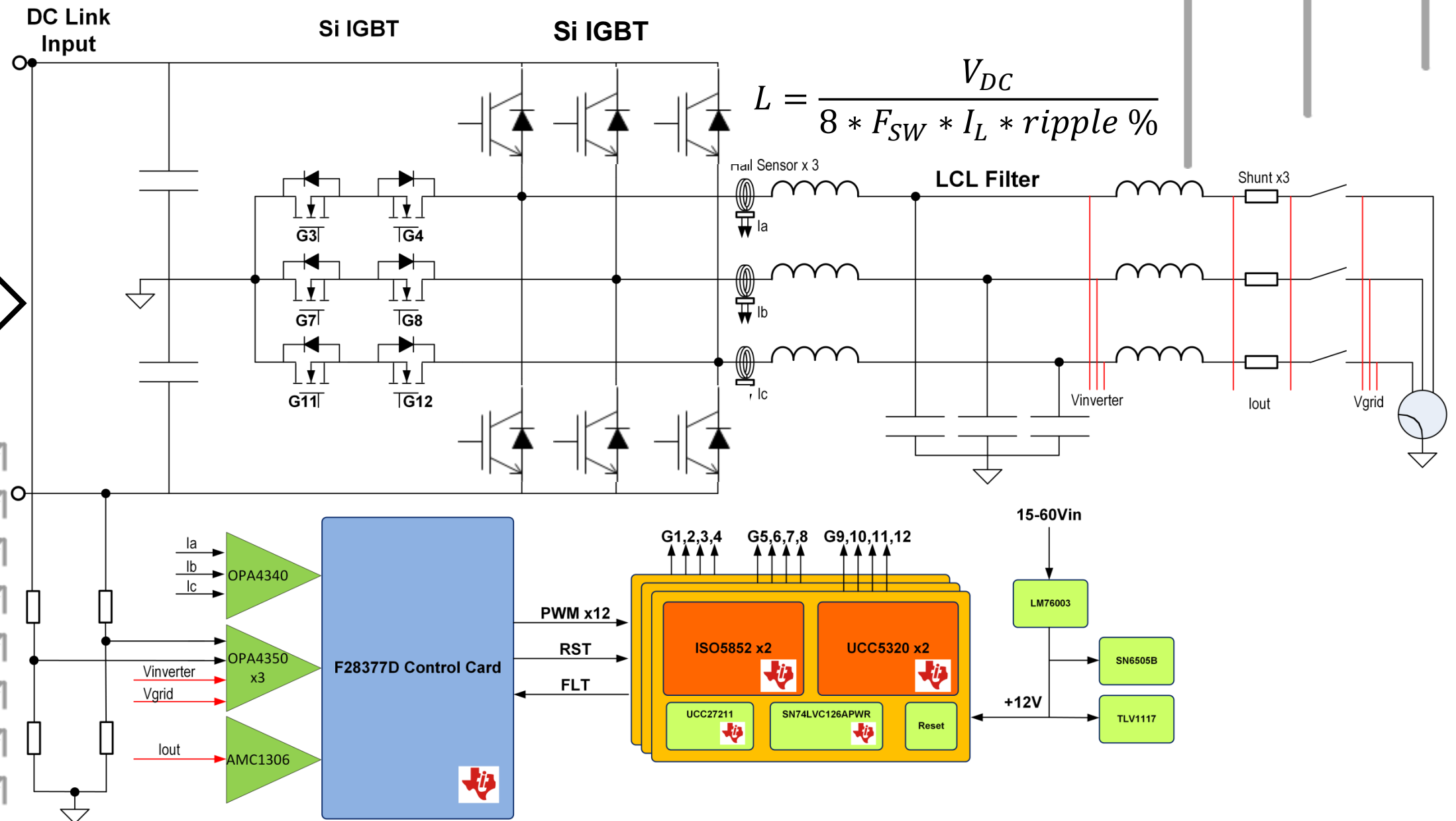
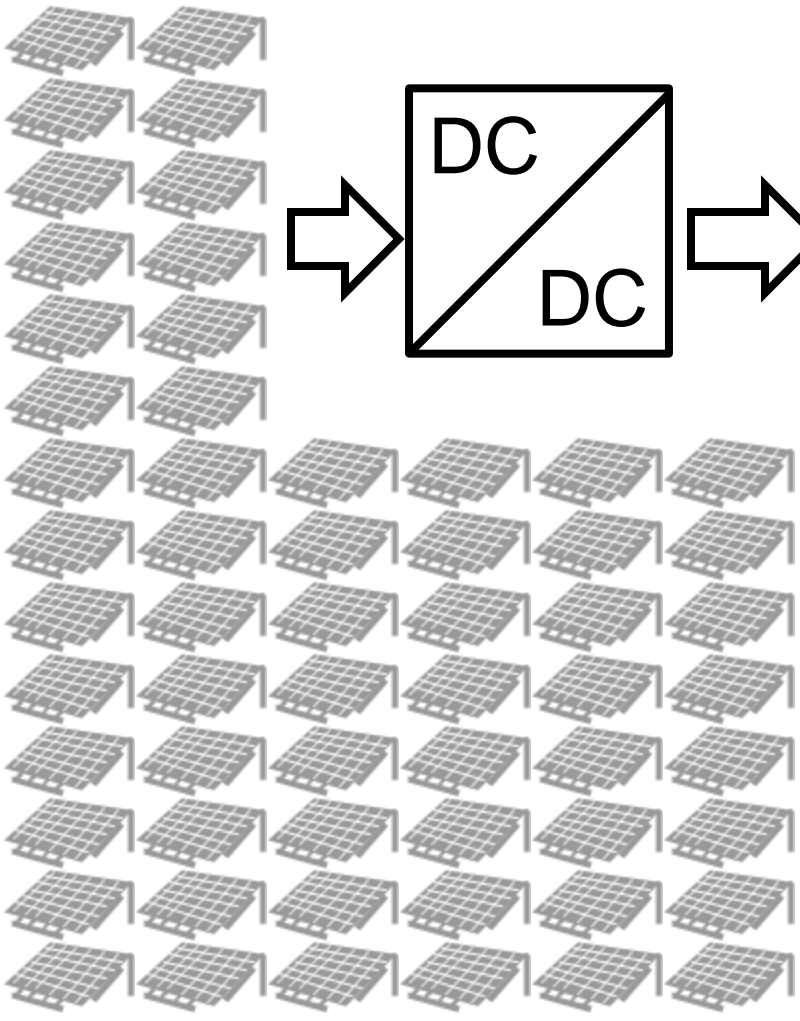
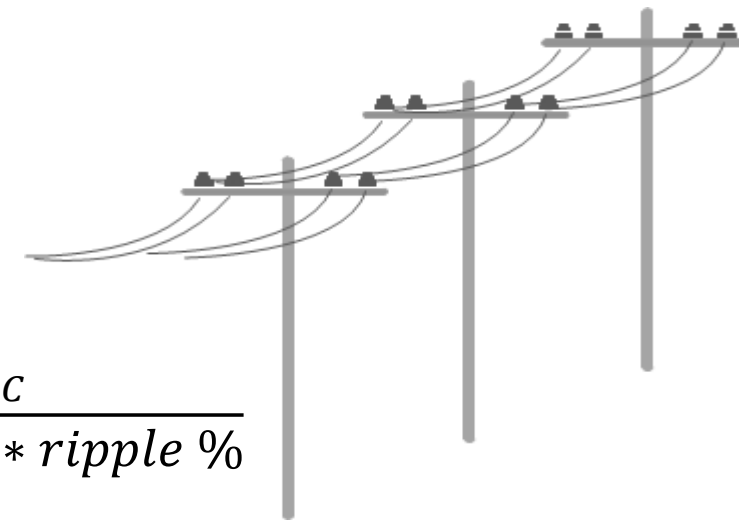
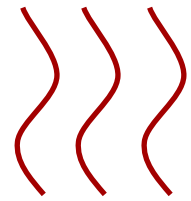
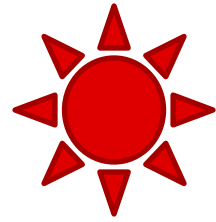
Three Phase Power Factor Correction

- $\Delta i_{ppmax} = \frac{V_{bus} * T_S}{2 * 4 * L_i} \Rightarrow L_i = \frac{V_{bus}}{4 * F_{SW} * \Delta i_{ppmax}}$
- Inductor size is inversely proportional to switching frequency
- **Slower $F_{SW} \Rightarrow$ Larger inductors**
- Line filter attenuates fundamental switching frequency and harmonics
- Attenuation at F_{SW} is proportional to filter component size, # of stages
- **Slower $F_{SW} \Rightarrow$ Bigger EMI filter**

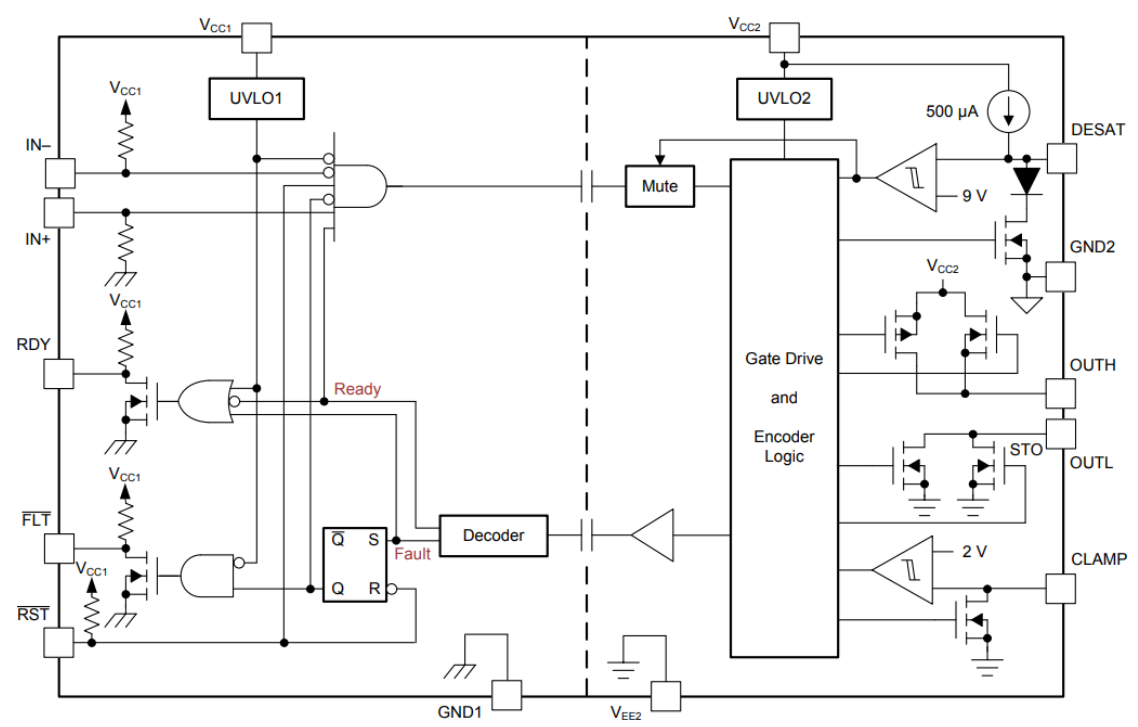
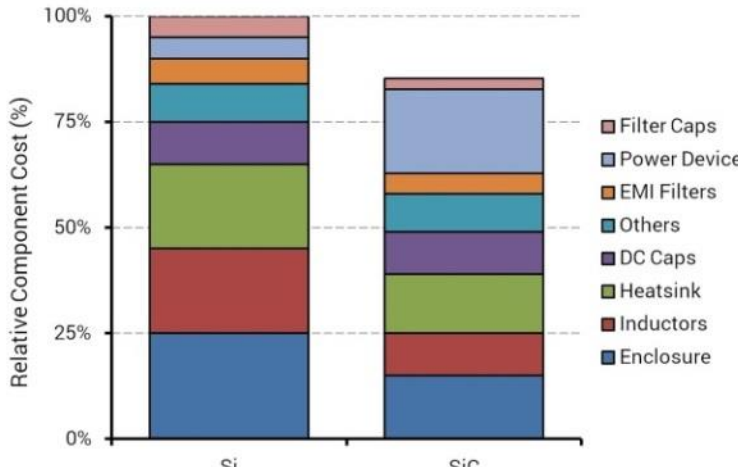
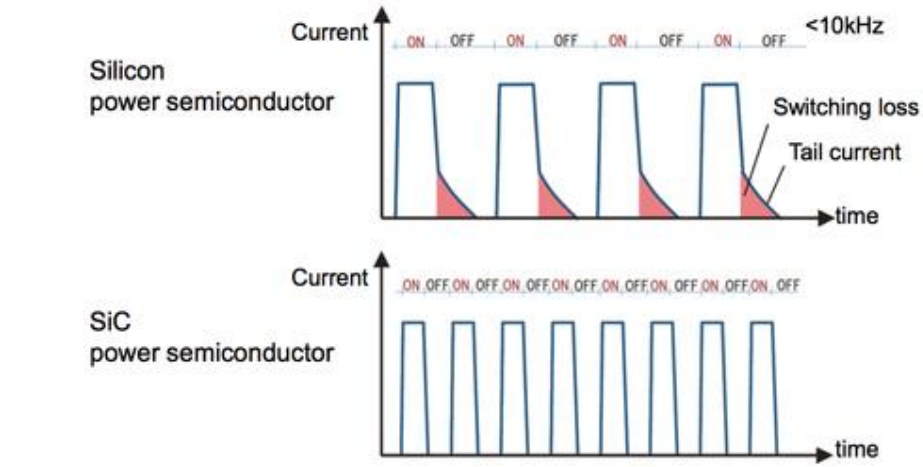
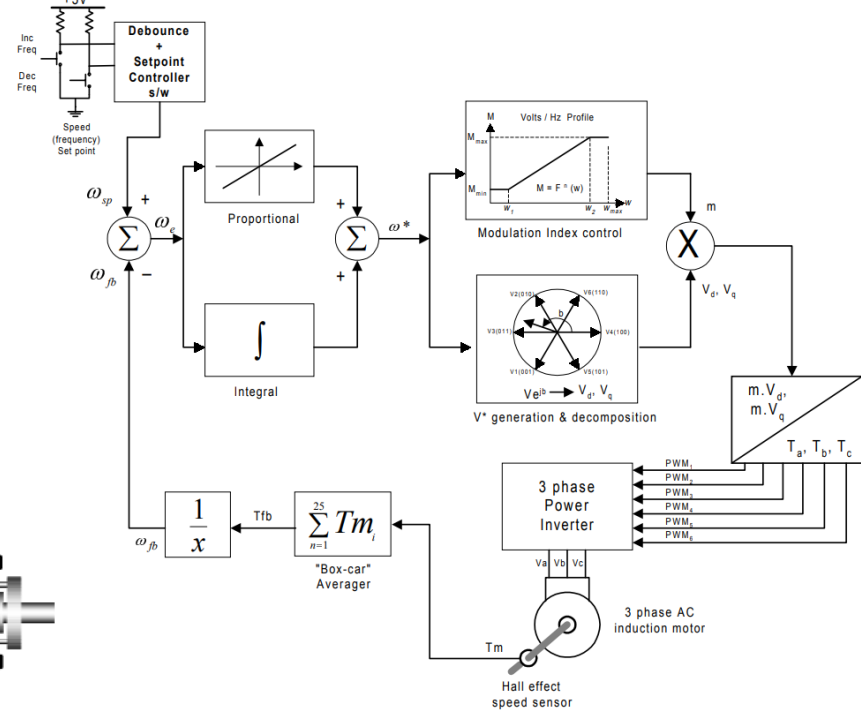
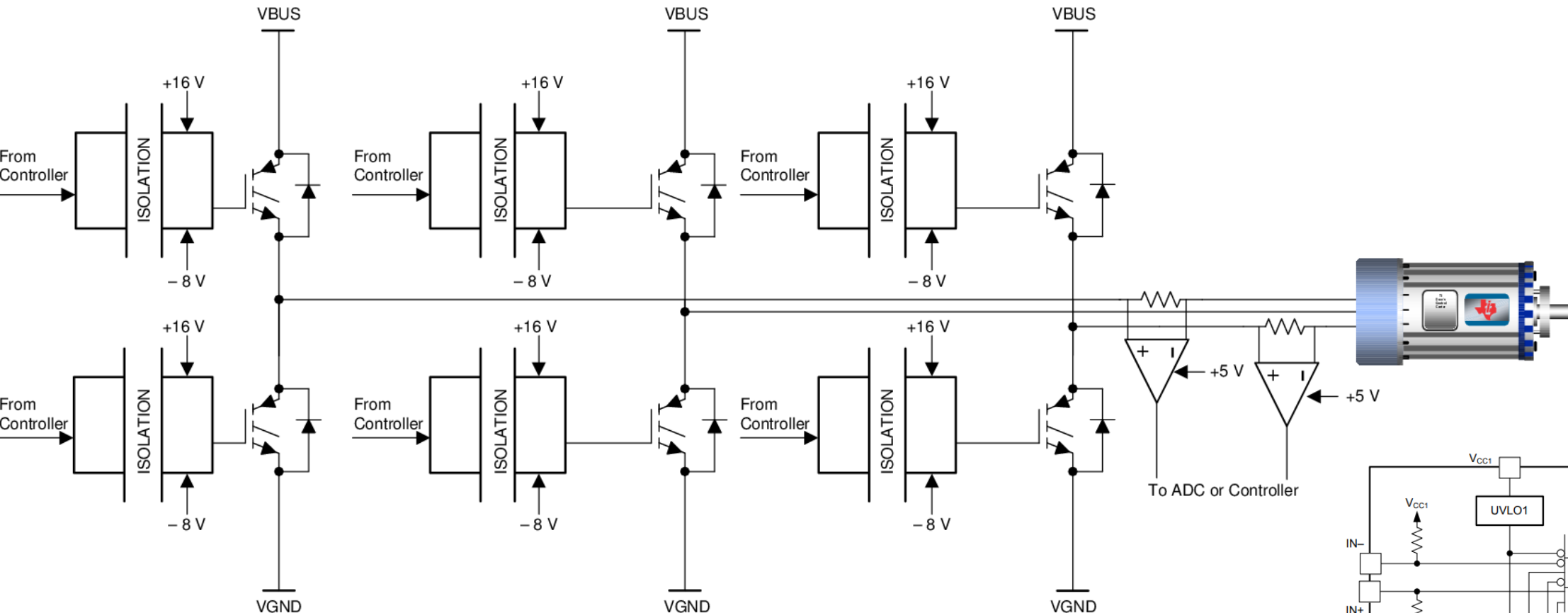
Size for $F_{SW} / 2$



Solar String Inverter

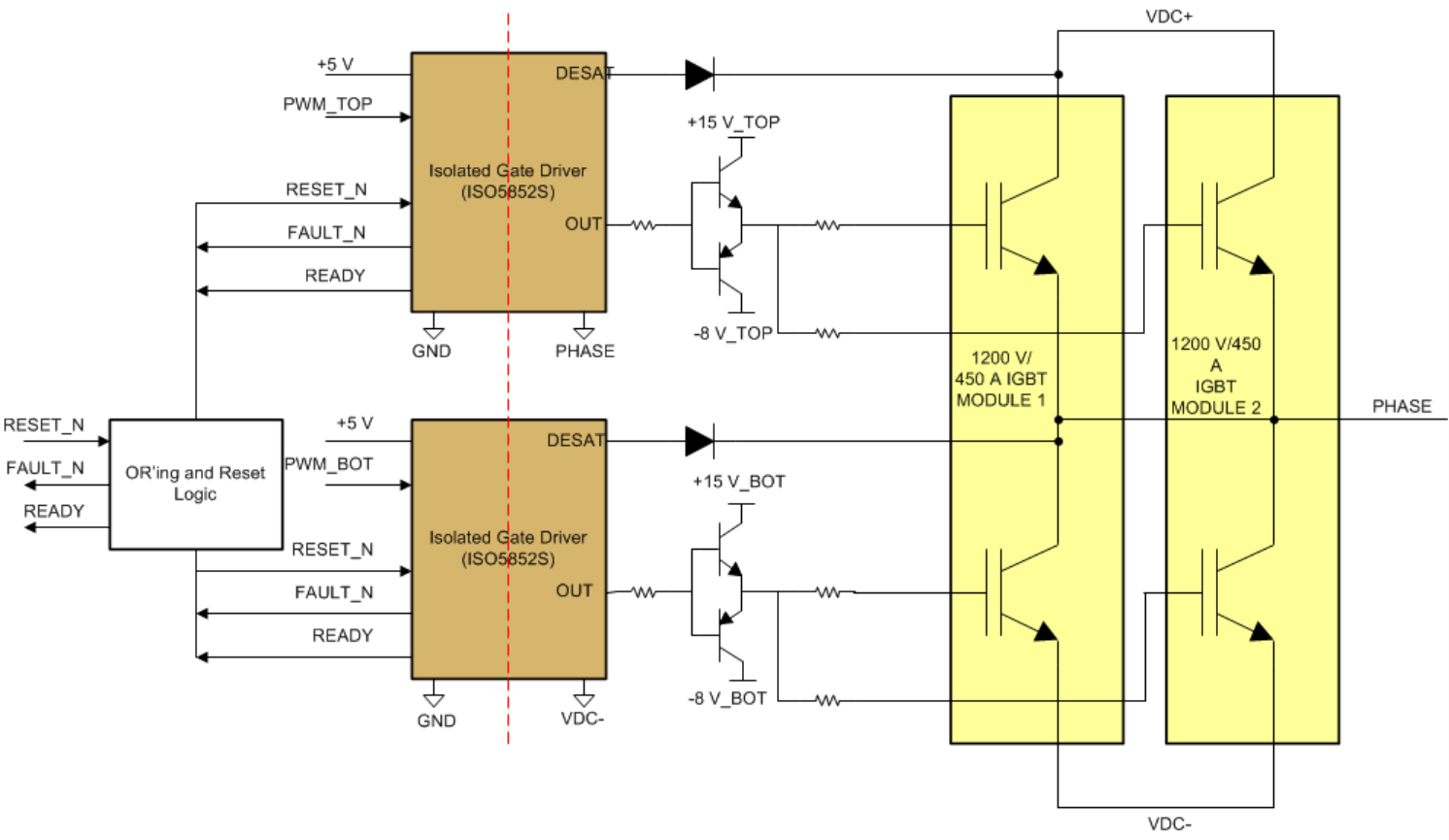
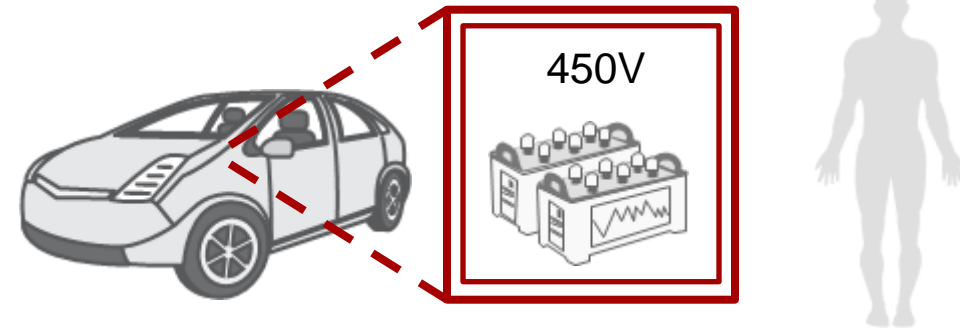


Motor Drive

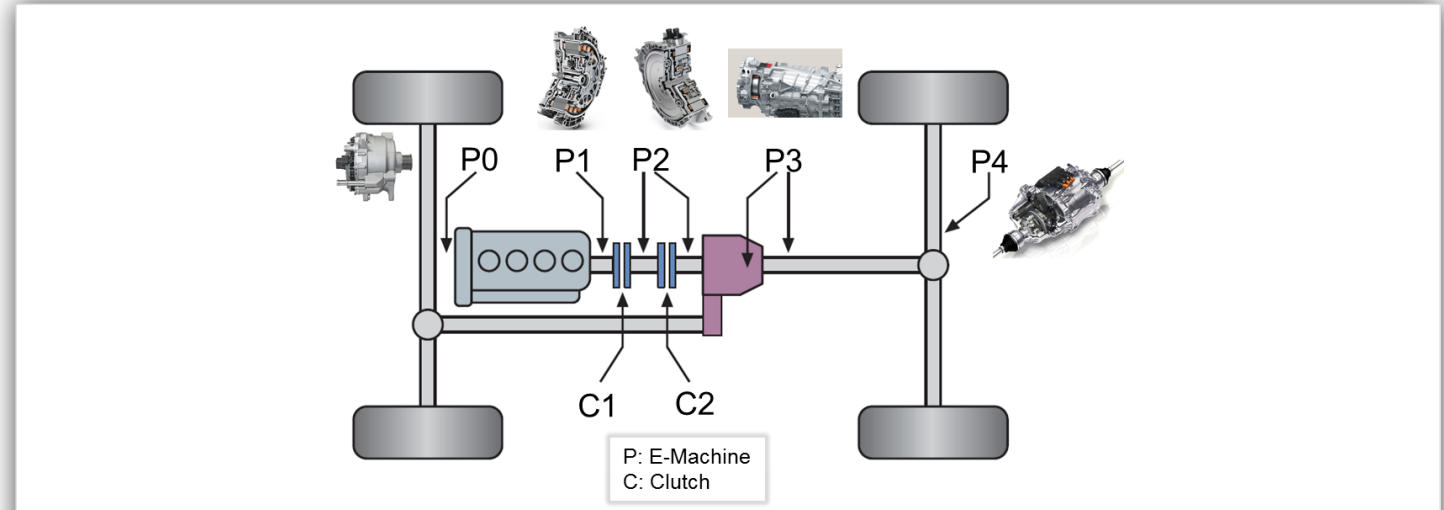


Traction Inverters

Reinforced Isolation



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E-MACHINE POSITION	ASIL RATING	COMMENT
P0	ASIL-B/C	Basic level of (48V) hybridization (BSG)
P1	ASIL-B/C	E-Machine at the crankshaft, very limited electric only drive
P2	ASIL-B/C	E-Machine placed in between combustion engine and transmission. Could be used for 48V and HV systems (ISG)
P3	ASIL-C/D	Transmission integrated E-Machine (ISG)
P4	ASIL-C/D	E-Axle, adds electric propulsion to the axle directly. Enables 4(A)WD. Could be used for pure electric vehicles

ASIL rating derived from ISO 26262

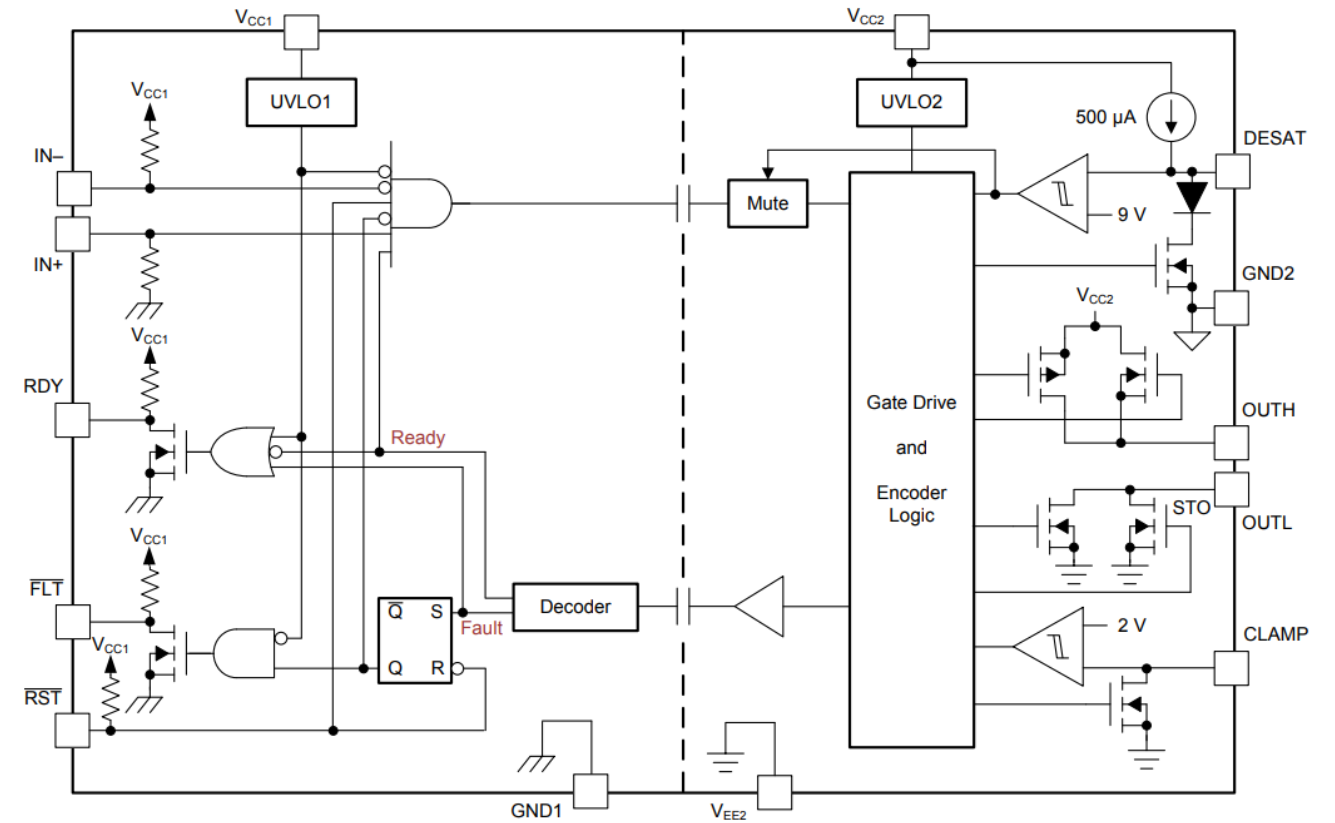
Looking Ahead

7.10 Switching Characteristics

Over recommended operating conditions unless otherwise noted. All typical values are at $T_A = 25^\circ\text{C}$, $V_{CC1} = 5\text{ V}$, $V_{CC2} - \text{GND2} = 15\text{ V}$, $\text{GND2} - V_{EE2} = 8\text{ V}$

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
t_r	Output-signal rise time at OUTH	$C_{\text{LOAD}} = 1\text{ nF}$	12	18	35	ns
t_f	Output-signal fall time at OUTL	$C_{\text{LOAD}} = 1\text{ nF}$	12	20	37	ns
$t_{\text{PLH}}, t_{\text{PHL}}$	Propagation Delay	$C_{\text{LOAD}} = 1\text{ nF}$	76	110		ns
$t_{\text{sk-p}}$	Pulse skew $ t_{\text{PHL}} - t_{\text{PLH}} $	$C_{\text{LOAD}} = 1\text{ nF}$		20		ns
$t_{\text{sk-pp}}$	Part-to-part skew	$C_{\text{LOAD}} = 1\text{ nF}$		30 ⁽¹⁾		ns
$t_{\text{GF}}(\text{IN}/\text{RST})$	Glitch filter on IN+, IN-, RST	$C_{\text{LOAD}} = 1\text{ nF}$	20	30	40	ns
$t_{\text{DS}}(90\%)$	DESAT sense to 90% $V_{\text{OUTH/L}}$ delay	$C_{\text{LOAD}} = 10\text{ nF}$	553	760		ns
$t_{\text{DS}}(10\%)$	DESAT sense to 10% $V_{\text{OUTH/L}}$ delay	$C_{\text{LOAD}} = 10\text{ nF}$	2	3.5		μs
$t_{\text{DS}}(\text{GF})$	DESAT-glitch filter delay	$C_{\text{LOAD}} = 1\text{ nF}$		330		ns
$t_{\text{DS}}(\text{FLT})$	DESAT sense to FLT-low delay	See Figure 46			1.4	μs
t_{LEB}	Leading-edge blanking time	See Figure 44 and Figure 45	310	400	480	ns
$t_{\text{GF}}(\text{RST}/\text{FLT})$	Glitch filter on RST for resetting FLT		300		800	ns
C_i	Input capacitance ⁽²⁾	$V_i = V_{CC1} / 2 + 0.4 \times \sin(2\pi ft)$, $f = 1\text{ MHz}$, $V_{CC1} = 5\text{ V}$		2		pF
CMTI	Common-mode transient immunity	$V_{\text{CM}} = 1500\text{ V}$, see Figure 47	100	120		kV/ μs

- (1) Measured at same supply voltage and temperature condition
 (2) Measured from input pin to ground.



Thanks for your time!
Please try the quiz.

Applications for Isolated Gate Drivers

Multiple Choice Quiz

TI Precision Labs – Isolation

Quiz: Applications for Isolated Gate Drivers

- 1. _____ must be used for the interface between high voltage and user-accessible circuitry (like connectors or communications ports) to meet many equipment safety standards.**
 - a. Reinforced isolation
 - b. Line drivers
 - c. Fiber optics
 - d. Low-voltage microcontrollers
- 2. _____ converts stable, monofrequency AC power to stable, clean DC power; _____ converts stable, clean DC power to stable, monofrequency AC power**
 - a. Solar string inverters / Motor drives
 - b. Power factor correction circuits / Traction inverters
 - c. Power factor correction circuits / Solar string inverters
 - d. Motor drives perform both functions
- 3. Thanks to their high voltage ratings and high current capability, _____ have been historically used in switching power systems up to hundreds of kilowatts**
 - a. Silicon carbide transistors
 - b. Insulated-gate bipolar transistors (IGBTs)
 - c. Silicon MOSFETs
 - d. Gallium nitride transistors

Quiz: Applications for Isolated Gate Drivers

4. **The high-voltage bus in solar string inverter designs has been _____ over time because _____**
- Increasing; it reduces I^2R losses and component size
 - Increasing; it increases switching frequency
 - Decreasing; it becomes easier to use inexpensive non-isolated gate drivers
 - Decreasing; it permits the use of faster, lower-voltage MOSFETs
5. **Silicon carbide MOSFETs are one potential way to improve size, cost, and performance of motor drives and traction inverters. It requires gate drivers that can:**
- Operate at automotive temperature ranges of -40°C to 125°C to enable high-temperature applications
 - Switch with low propagation delay and low pulse width distortion to enable fast switching
 - Integrate protection features to minimize external component count and cost
 - Both b and c
6. **Traction inverters help to define the next generation of isolated gate drivers because:**
- Automotive ASIL ratings place strict requirements on critical systems, including gate drivers
 - Size, cost, and heatsinking material constraints emphasize gate drivers with highly-integrated features
 - Silicon carbide MOSFETs have unique drive requirements compared to IGBTs or MOSFETs
 - All of the above

Applications for Isolated Gate Drivers

Multiple Choice Quiz – Solutions

TI Precision Labs – Isolation

Quiz: Applications for Isolated Gate Drivers

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 - b. Line drivers
 - c. Fiber optics
 - d. Low-voltage microcontrollers
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 - c. **Power factor correction circuits / Solar string inverters**
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